

# F DN308P

## P-Channel 2.5V Specified PowerTrench® MOSFET

### General Description

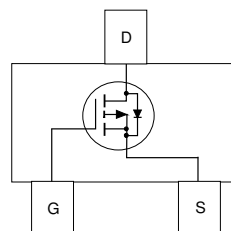
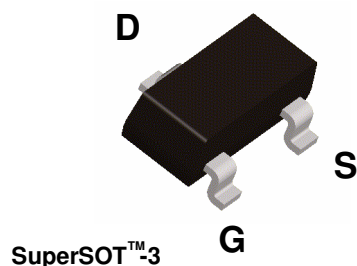
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

### Applications

- Power management
- Load switch
- Battery protection

### Features

- –20 V, –1.5 A.  $R_{DS(ON)} = 125\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$   
 $R_{DS(ON)} = 190\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
- Fast switching speed
- High performance trench technology for extremely low  $R_{DS(ON)}$
- SuperSOT™ -3 provides low  $R_{DS(ON)}$  and 30% higher power handling capability than SOT23 in the same footprint



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	–20	V
V <sub>GSS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a) – Pulsed	–1.5	A
		–10	
P <sub>D</sub>	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5	W
		0.46	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	–55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
308	F DN308P	7"	8mm	3000 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = −250 μA	−20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = −250 μA, Referenced to 25°C		−13		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = −16 V, V <sub>GS</sub> = 0 V			−1	μA
I <sub>GSSF</sub>	Gate–Body Leakage, Forward	V <sub>GS</sub> = 12 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate–Body Leakage, Reverse	V <sub>GS</sub> = −12 V V <sub>DS</sub> = 0 V			−100	nA
On Characteristics (Note 2)						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = −250 μA	−0.6	−1.0	−1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = −250 μA, Referenced to 25°C		3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	V <sub>GS</sub> = −4.5 V, I <sub>D</sub> = −1.5 A V <sub>GS</sub> = −2.5 V, I <sub>D</sub> = −1.3 A V <sub>GS</sub> = −4.5 V, I <sub>D</sub> = −1.5A T <sub>J</sub> =125°C		86 136 114	125 190 178	mΩ
I <sub>D(on)</sub>	On–State Drain Current	V <sub>GS</sub> = −4.5 V, V <sub>DS</sub> = −5 V	−5			A
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = −5 V, I <sub>D</sub> = −1.5 A		12		S
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = −10 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		341		pF
C <sub>oss</sub>	Output Capacitance			83		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			43		pF
t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = −10 V, I <sub>D</sub> = −1 A, V <sub>GS</sub> = −4.5 V, R <sub>GEN</sub> = 6 Ω		8	16	ns
t <sub>r</sub>	Turn–On Rise Time			10	20	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			12	22	ns
t <sub>f</sub>	Turn–Off Fall Time			8	16	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = −10V, I <sub>D</sub> = −1.5 A, V <sub>GS</sub> = −4.5 V		3.8	5.4	nC
Q <sub>gs</sub>	Gate–Source Charge			0.8		nC
Q <sub>gd</sub>	Gate–Drain Charge			1.0		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I <sub>S</sub>	Maximum Continuous Drain–Source Diode Forward Current				−0.42	A
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = −0.42 (Note 2)		−0.7	−1.2	V

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $250^\circ\text{C/W}$  when mounted on a  $0.02\text{ in}^2$  pad of 2 oz. copper.



b)  $270^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

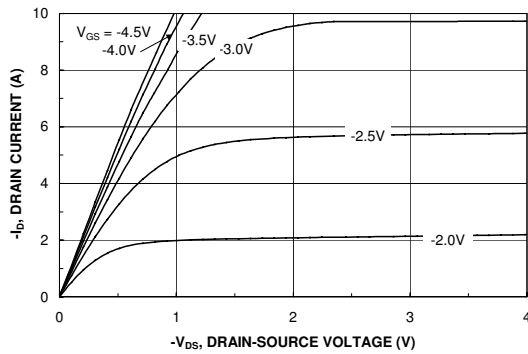


Figure 1. On-Region Characteristics.

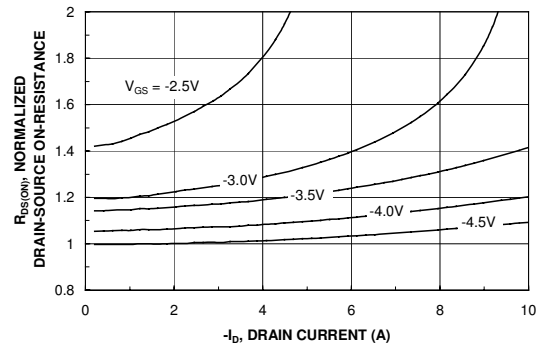


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

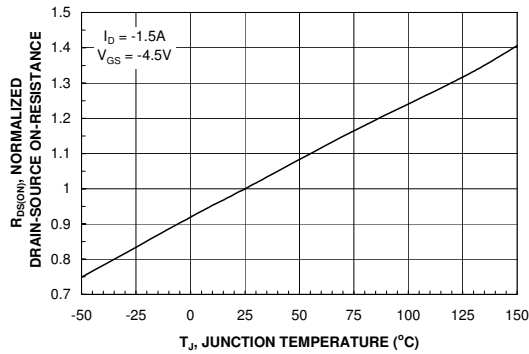


Figure 3. On-Resistance Variation with Temperature.

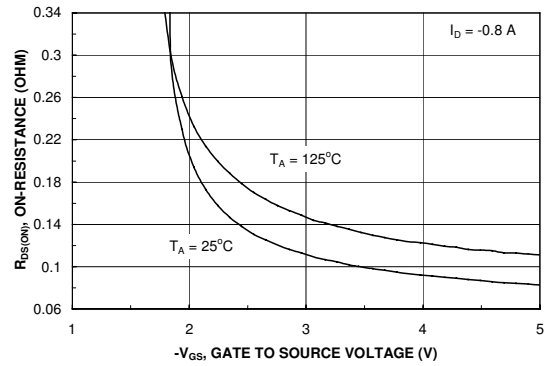


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

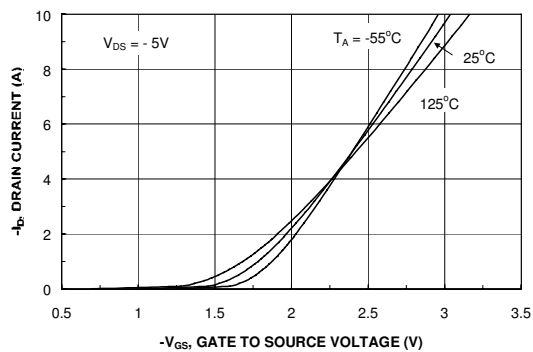


Figure 5. Transfer Characteristics.

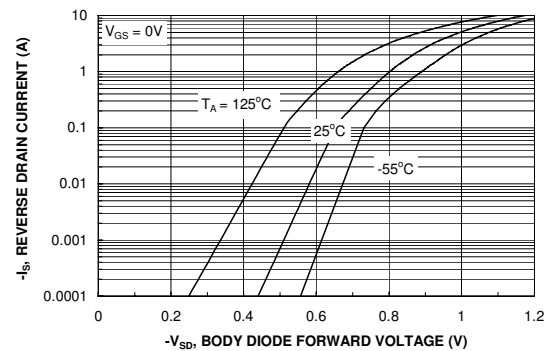


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

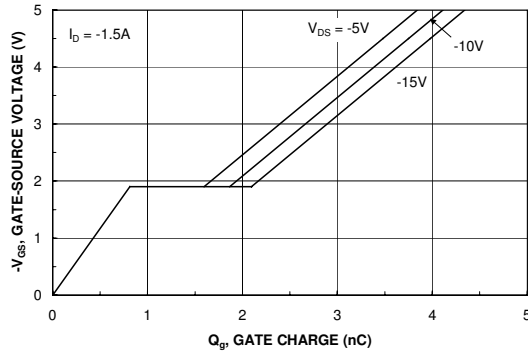


Figure 7. Gate Charge Characteristics.

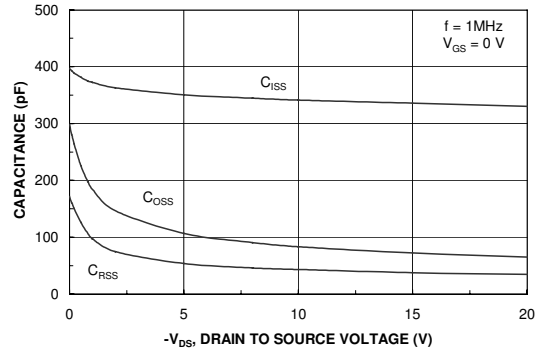


Figure 8. Capacitance Characteristics.

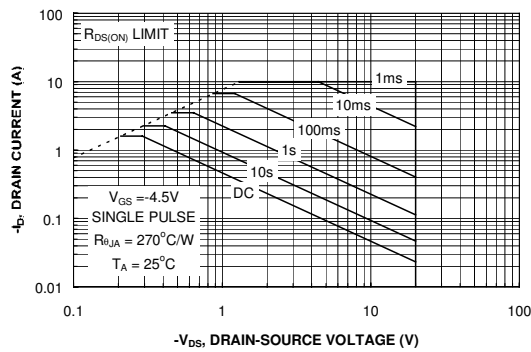


Figure 9. Maximum Safe Operating Area.

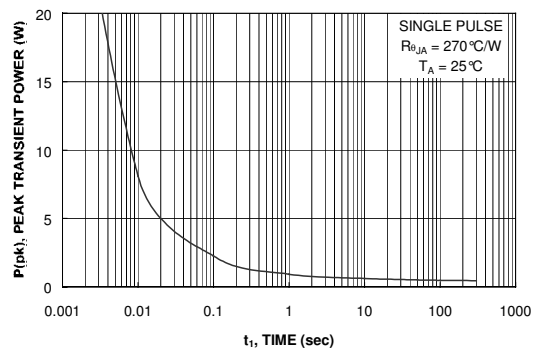


Figure 10. Single Pulse Maximum Power Dissipation.

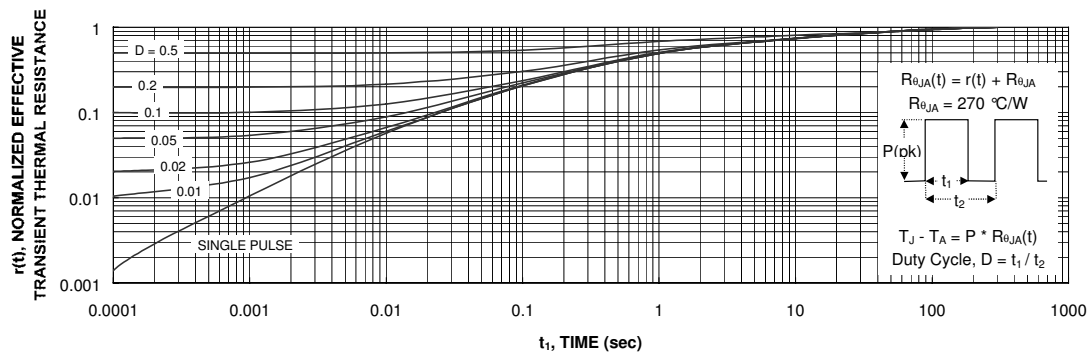


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

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DOME™	ISOPLANAR™	Quiet Series™	
E <sup>2</sup> CMOS™	MICROWIRE™	SILENT SWITCHER®	
EnSigna™	OPTOLOGIC™	SMART START™	
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